



Electrical Characteristics (Wafer Form)

Parameter	Description	Guaranteed (Min/Max)	Test Conditions
V_{FM}	Forward Voltage	1.0V Max.	$T_J = 25^{\circ}\text{C}$, $I_F = 10.0\text{A}$
BV_R	Reverse Breakdown Voltage	600V Min.	$T_J = 25^{\circ}\text{C}$, $I_R = 250\mu\text{A}$
I_{RM}	Reverse Leakage Current	25 μA Max.	$T_J = 25^{\circ}\text{C}$, $V_R = 600\text{V}$

Mechanical Data

Norminal Backmetal Composition, Thickness:	Cr-Ni-Ag (1kA-4kA-6kA)
Norminal Front Metal Composition, Thickness:	99% Al, 1% Si (3 microns)
Dimensions:	0.257" x 0.205"
Wafer Diameter:	125mm, with std. < 100 > flat
Wafer thickness:	.015" + / -.003"
Relevant Die Mechanical Dwg. Number	01-5163
Minimum Street Width	100 Microns
Reject Ink Dot Size	0.25mm Diameter Minimum
Ink Dot Location	See Die Outline drawing below
Recommended Storage Environment:	Store in original container, in dessicated nitrogen, with no contamination

Reference Standard IR packaged part (for design) : GA75TS60U

Die Outline

